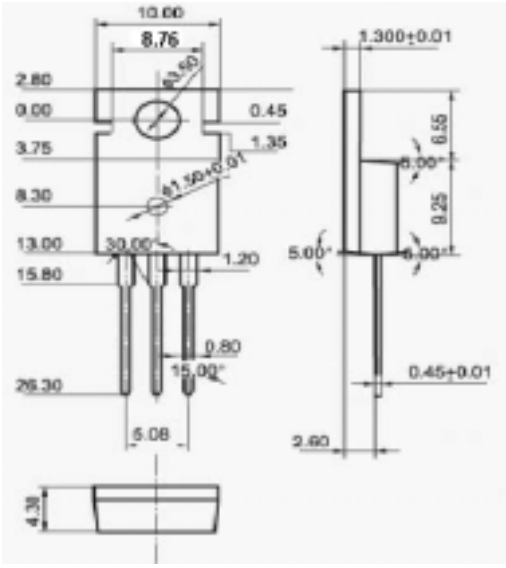
IRF634

N-channel mosfet transistor

1 2 3

◆ Features

- With TO-220 package
- Simple drive requirements
- Fast switching
- V_{DSS}=250V; $R_{DS(ON)}$≤0.45Ω;I_D=8.1A
- 1.gate 2.drain 3.source



TO-220

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{DSS}	Drain-source voltage (V_{GS}=0)	250	V
V_{GS}	Gate-source voltage	±20	V
I_D	Drain Current-continuous@ T_C=25℃	8.1	A
P_{tot}	Total Dissipation@T_C=25℃	74	W
T_j	Max. Operating Junction temperature	150	℃
T_{stg}	Storage temperature	-65~150	℃

◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS}=0; I_D=0.25mA	250		V
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}= V_{GS}; I_D=0.25mA	2	4	V
$R_{DS(ON)}$	Drain-source on-stage resistance	V_{GS}=10V; I_D=5.1A		450	mΩ
I_{GSS}	Gate source leakage current	V_{GS}=±20V;V_{DS}=0		±100	nA
I_{DSS}	Zero gate voltage drain current	V_{DS}=250V; V_{GS}=0		25	uA
V_{SD}	Diode forward voltage	I_F=8.1A; V_{GS}=0		2.0	V